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November 2013

# FCP16N60N / FCPF16N60NT N-Channel SupreMOS<sup>®</sup> MOSFET 600 V, 16 A, 199 m $\Omega$

#### **Features**

- $R_{DS(on)}$  = 170  $m\Omega$  (Typ.) @  $V_{GS}$  = 10 V,  $I_D$  = 8 A
- Ultra Low Gate Charge (Typ. Q<sub>q</sub> = 40.2 nC)
- Low Effective Output Capacitance (Typ. C<sub>oss(eff.)</sub> = 176 pF)
- 100% Avalanche Tested
- · RoHS Compliant

## **Application**

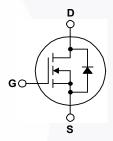
- LCD/LED/PDP TV
- · Lighting
- · Solar Inverter
- · AC-DC Power Supply

## Description

The SupreMOS® MOSFET is Fairchild Semiconductor's next generation of high voltage super-junction (SJ) technology employing a deep trench filling process that differentiates it from the conventional SJ MOSFETs. This advanced technology and precise process control provides lowest Rsp on-resistance, superior switching performance and ruggedness. SupreMOS MOSFET is suitable for high frequency switching power converter applications such as PFC, server/telecom power, FPD TV power, ATX power, and industrial power applications.







## Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol		Parameter		FCP16N60N	FCPF16N60NT	Unit	
$V_{DSS}$	Drain to Source Voltage	Drain to Source Voltage			600		
$V_{GSS}$	Gate to Source Voltage			±	30	V	
	Drain Current	- Continuous (T <sub>C</sub> = 25°C)		16.0 16.0*		^	
ID	Drain Current	- Continuous (T <sub>C</sub> = 100°C)		10.1	10.1*	Α	
I <sub>DM</sub>	Drain Current	- Pulsed	(Note 1)	48.0	48.0*	Α	
E <sub>AS</sub>	Single Pulsed Avalanche E	nergy	(Note 2)	3	55	mJ	
I <sub>AR</sub>	Avalanche Current		(Note 1)	5	.3	Α	
E <sub>AR</sub>	Repetitive Avalanche Ener	gy	(Note 1)	1.	34	mJ	
dv/dt	MOSFET dv/dt			1	00	V/ns	
uv/ut	Peak Diode Recovery dv/d	lt	(Note 3)	2	20	V/ns	
В	Dower Dissipation	(T <sub>C</sub> = 25°C)		134.4	35.7	W	
$P_D$	Power Dissipation	- Derate Above 25°C		1.08	0.29	W/°C	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range			-55 to	+150	°С	
TL	Maximum Lead Temperatu	re for Soldering, 1/8" from Case for	5 Seconds	3	00	°C	

<sup>\*</sup>Drain current limited by maximum junction temperature.

#### **Thermal Characteristics**

Symbol	Parameter	FCP16N60N	FCPF16N60NT	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.93	3.5	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	62.5	C/VV

## **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FCP16N60N	FCP16N60N	TO-220	Tube	N/A	N/A	50 units
FCPF16N60NT	FCPF16N60NT	TO-220F	Tube	N/A	N/A	50 units

## **Electrical Characteristics** T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	cteristics					
$BV_{DSS}$	Drain to Source Breakdown Voltage	$I_D = 1 \text{ mA}, V_{GS} = 0V, T_C = 25^{\circ}C$	600	-	-	V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 1 mA, Referenced to 25°C	-	0.73	-	V/°C
	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 480 V, V <sub>GS</sub> = 0 V	-	-	10	
IDSS	Zero Gate voltage Drain Current	$V_{DS} = 480 \text{ V}, V_{GS} = 0 \text{ V}, T_{C} = 125^{\circ}\text{C}$	-	-	100	μА
I <sub>GSS</sub>	Gate to Body Leakage Current	V <sub>GS</sub> = ±30 V, V <sub>DS</sub> = 0 V	-	-	±100	nA

#### **On Characteristics**

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu\text{A}$	2.0	-	4.0	V
R <sub>DS(on)</sub>	Static Drain to Source On Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 8 A	1	0.170	0.199	Ω
9 <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 40 V, I <sub>D</sub> = 8 A	ı	13	-	S

## **Dynamic Characteristics**

C <sub>iss</sub>	Input Capacitance	V 400 V V 0 V	-	1630	2170	pF
C <sub>oss</sub>	Output Capacitance	$V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1  MHz	-\	70	95	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	1 - 1 1011 12	- \	5	10	pF
C <sub>oss</sub>	Output Capacitance	$V_{DS} = 380 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	- \	40	60	pF
C <sub>oss(eff.)</sub>	Effective Output Capacitance	V <sub>DS</sub> = 0 V to 480 V, V <sub>GS</sub> = 0 V	-	176	-	pF
Q <sub>g(tot)</sub>	Total Gate Charge at 10V	V <sub>DS</sub> = 380 V, I <sub>D</sub> = 8 A,	-	40.2	52.3	nC
$Q_{gs}$	Gate to Source Gate Charge	V <sub>GS</sub> = 10 V	-	6.7	-	nC
$Q_{gd}$	Gate to Drain "Miller" Charge	(Note 4)	-	12.9	-	nC
ESR	Equivalent Series Resistance (G-S)	f = 1 MHz		2.9		Ω

#### **Switching Characteristics**

	_						
t <sub>d(on)</sub>	Turn-On Delay Time			-/	15.8	41.6	ns
t <sub>r</sub>	Turn-On Rise Time	$V_{DD} = 380 \text{ V}, I_D = 8 \text{ A},$		-	15.5	41.0	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	$V_{GS}$ = 10 V, $R_{G}$ = 4.7 $\Omega$		/ -	60.3	130.6	ns
t <sub>f</sub>	Turn-Off Fall Time		(Note 4)	-	20.2	50.4	ns

#### **Drain-Source Diode Characteristics**

$I_S$	Maximum Continuous Drain to Source Diode Forward Current		-	-	16	Α
I <sub>SM</sub>	Maximum Pulsed Drain to Source Diode Fo	rward Current	-	-	48	Α
$V_{SD}$	Drain to Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>SD</sub> = 8 A	-	-	1.2	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>SD</sub> = 8 A,	-	319	-	ns
Q <sub>rr</sub>	Reverse Recovery Charge	$dI_F/dt = 100 A/\mu s$	-	4.4	/// -	μС

#### Notes:

- 1. Repetitive rating: pulse-width limited by maximum junction temperature.
- 2.  $I_{AS}$  = 5.3 A,  $R_G$  = 25  $\Omega$ , starting  $T_J$  = 25 $^{\circ}$ C.
- 3. I  $_{SD}$   $\leq$  16 A, di/dt  $\leq$  200 A/ $\mu$ s, V  $_{DD}$  = 380 V, starting T  $_{J}$  = 25°C
- 4. Essentially independent of operating temperature typical characteristics.

## **Typical Performance Characteristics**

Figure 1. On-Region Characteristics

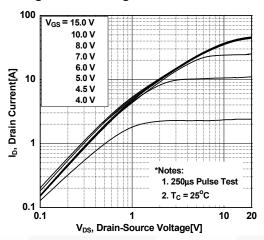


Figure 3. On-Resistance Variation vs.
Drain Current and Gate Voltage

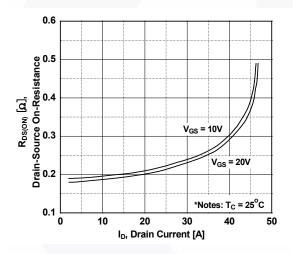


Figure 5. Capacitance Characteristics

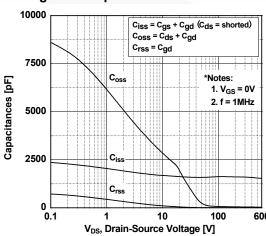


Figure 2. Transfer Characteristics

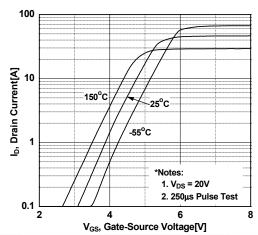


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

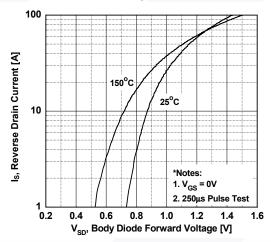
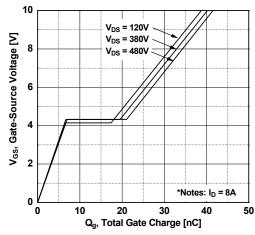


Figure 6. Gate Charge Characteristics



## **Typical Performance Characteristics** (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

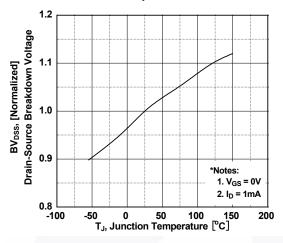


Figure 9. Maximum Safe Operating Area for FCP16N60N

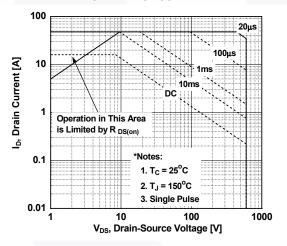


Figure 11. Maximum Drain Current vs. Case Temperature

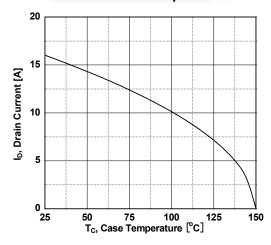


Figure 8. On-Resistance Variation vs. Temperature

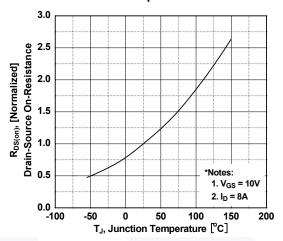
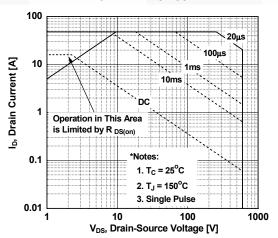


Figure 10. Maximum Safe Operating Area for FCPF16N60NT



## **Typical Performance Characteristics** (Continued)

Figure 12. Transient Thermal Response Curve for FCP16N60N

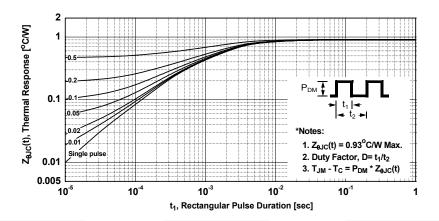
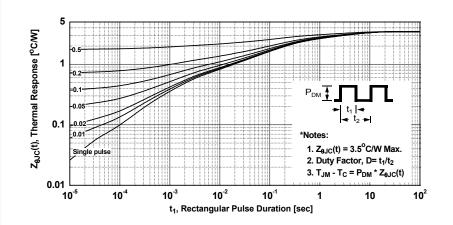


Figure 13. Transient Thermal Response Curve for FCPF16N60NT



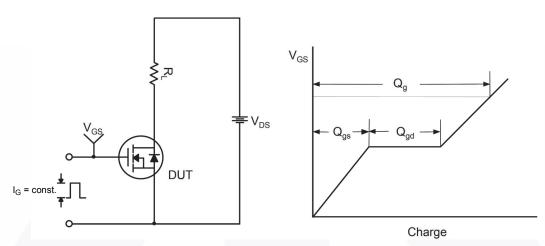


Figure 14. Gate Charge Test Circuit & Waveform

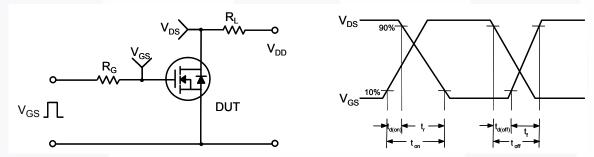


Figure 15. Resistive Switching Test Circuit & Waveforms

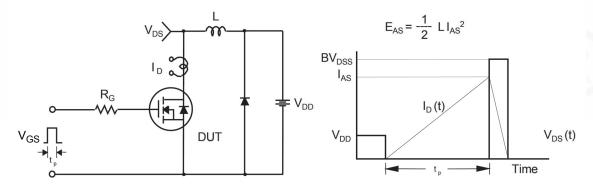


Figure 16. Unclamped Inductive Switching Test Circuit & Waveforms

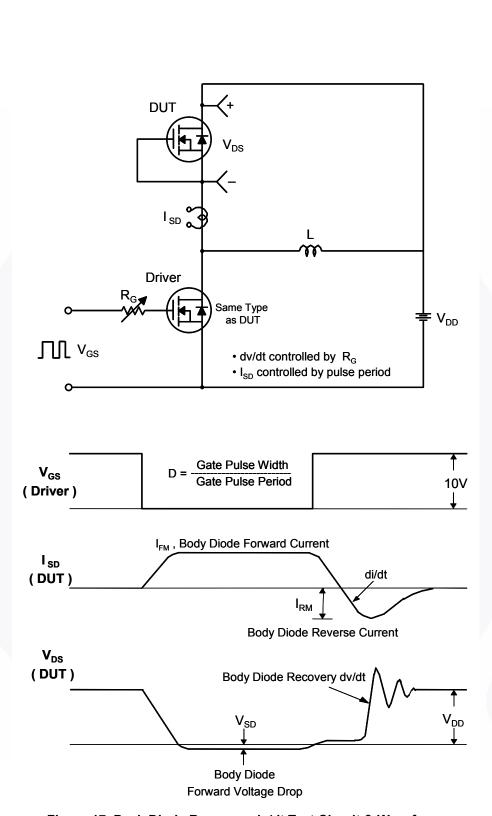


Figure 17. Peak Diode Recovery dv/dt Test Circuit & Waveforms

#### **Mechanical Dimensions**

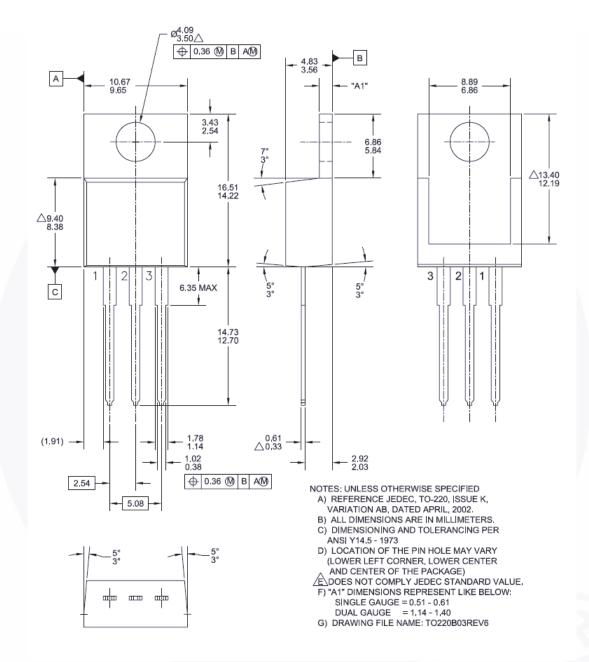


Figure 18. TO-220, Molded, 3-Lead, Jedec Variation AB

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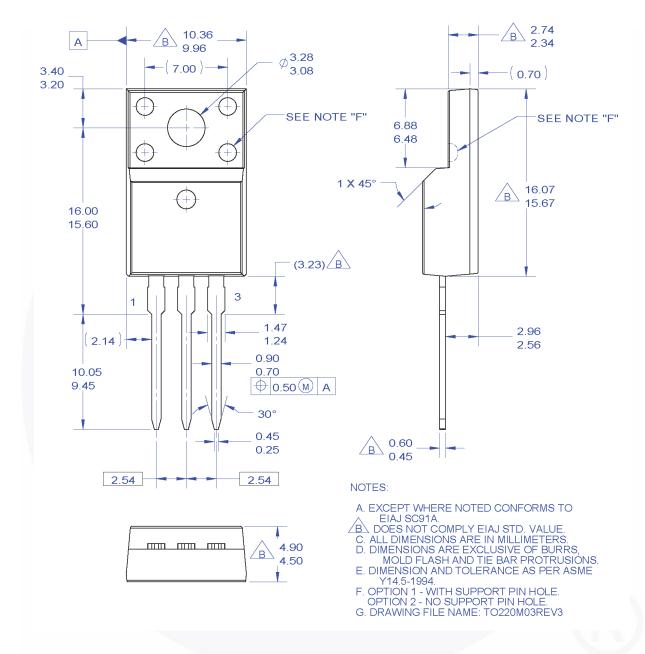


Figure 19. TO220, Molded, 3-Lead, Full Pack, EIAJ SC91, Straight Lead

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